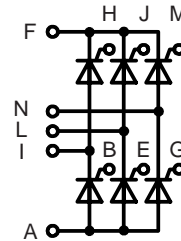


Three Phase Rectifier Bridge

$I_{dAV} = 39 \text{ A}$
 $V_{RRM} = 600-1200 \text{ V}$

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
700	600	VTO 39-06ho7
900	800	VTO 39-08ho7
1300	1200	VTO 39-12ho7



E72873



Symbol	Conditions	Maximum Ratings	
I_{dAV} ①	$T_C = 85^\circ\text{C}$, module	39	A
I_{TAVM}	$T_C = 85^\circ\text{C}$; (180° sine ; per thyristor)	16	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine	200 A
		t = 8.3 ms (60 Hz), sine	210 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine	180 A
		t = 8.3 ms (60 Hz), sine	190 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine	200 A ² s
		t = 8.3 ms (60 Hz), sine	150 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50Hz, $t_p = 200\mu\text{s}$ $V_D = \frac{2}{3} V_{DRM}$ $I_G = 0.15 \text{ A}$ $di_G/dt = 0.15 \text{ A}/\mu\text{s}$	repetitive, $I_T = 20 \text{ A}$	100 A/ μs
		non repetitive, $I_T = I_{TAVM}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = \frac{2}{3} V_{DRM}$	500 V/ μs
V_{RGM}		10	V
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$	≤ 5 W
		$t_p = 300 \mu\text{s}$	≤ 2.5 W
P_{GAVM}		0.5	W
T_{VJ}		-40...+125	°C
T_{VJM}		125	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min	2500 V~
		t = 1 s	3000 V~
M_d	Mounting torque (M4)	1.5 - 2	Nm
		14 - 18	lb.in.
Weight	typ.	18	g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering

Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Small and light weight

Data according to IEC 60747 refer to a single diode/thyristor unless otherwise stated.

① for resistive load at bridge output.

IXYS reserves the right to change limits, test conditions and dimensions.

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Symbol	Conditions	Characteristic Values	
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5 mA
V_T	$I_T = 20 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.6 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85	V
r_T		27	m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	1.5 V
	$T_{VJ} = -40^\circ\text{C}$	\leq	2.5 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	25 mA
	$T_{VJ} = -40^\circ\text{C}$	\leq	50 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	\leq	0.2 V
I_{GD}		\leq	3 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.1 \text{ A}; di_G/dt = 0.1 \text{ A}/\mu\text{s}$	\leq	75 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	50 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.1 \text{ A}; di_G/dt = 0.1 \text{ A}/\mu\text{s}$	\leq	2 μs
R_{thJC}	per thyristor; DC	1.3	KW
	per module	0.22	KW
R_{thJH}	per thyristor; DC	1.8	KW
	per module	0.3	KW
d_s	Creeping distance on surface	11.2	mm
d_A	Creepage distance in air	5	mm
a	Max. allowable acceleration	50	m/s ²

Dimensions in mm (1 mm = 0.0394")

